

separating an upper portion of said semi-conductor substrate from said substrate along a line of relative weakness defined in or adjacent said second porous layer to obtain said thin film semi-conductor,

wherein said first porous layer and said second porous layer are formed by anodizing.

REMARKS

With this Fourth Preliminary Amendment, claims 74-159 are pending in this application. Of these claims, claims 74, 76-80, 103-104, 107-109, 124-126, 128-129, 134-144 and 154-159 are in independent form. Originally filed claims 1-73 have been cancelled, without prejudice or disclaimer thereof.

New claims 143-159 herein have been copied from U.S. Patent No. 6,426,274 (“‘274 patent”), which issued July 30, 2002. In particular, the claims herein correspond to the claims of the ‘274 patent as follows:

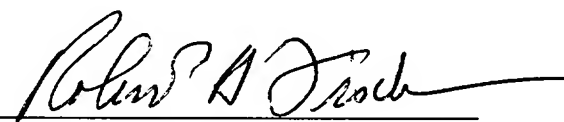
<u>‘274 Patent Claim</u>	<u>Subject Application Claim</u>
1	143
2	144
3	145
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18	159

In addition to the '274 patent claims copied herein, the subject application contains claims copied from three other patents: U.S. Patent Nos. 6,107,213, 6,194,245 and 6,326,280. A Request for Declaration of Interference, Proposed Count and Tables of Support will follow shortly.

In light of the foregoing, applicants respectfully request entry of this amendment.

Respectfully submitted,


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